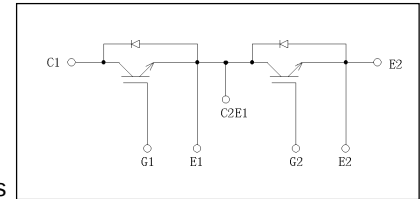


2MBI150U2A-060



IGBT Module U-Series 600V / 150A 2 in one-package

■ Equivalent Circuit Schematic



■ Features

- High speed switching
- Voltage drive
- Low inductance module structure

■ Applications

- Inverter for Motor drive
- AC and DC Servo drive amplifier
- Uninterruptible power supply
- Industrial machines, such as Welding machines

■ Maximum ratings and characteristics

● Absolute maximum ratings (at Tc=25°C unless otherwise specified)

Item			Symbol	Conditions	Rating	Unit
Collector-Emitter voltage			V _{CES}		600	V
Gate-Emitter voltage			V _{GES}		±20	V
Collector current			I _c	Continuous	150	A
			I _{cp}	1ms	300	
			-I _c		150	
			-I _c pulse		300	
Collector Power Dissipation			P _c	1 device	500	W
Junction temperature			T _j		+150	°C
Storage temperature			T _{stg}		-40 to +125	
Isolation voltage	between terminal and copper base *1		V _{iso}	AC:1min.	2500	VAC
Screw Torque		Mounting *2			3.5	N·m
		Terminals *2			3.5	

*1 : All terminals should be connected together when isolation test will be done.

*2 : Recommendable value : Mounting 2.5 to 3.5N·m(M5 or M5), Terminal 2.5 to 3.5 N·m(M5)

● Electrical characteristics (at Tj=25°C unless otherwise specified)

Item	Symbols	Conditions		Characteristics			Unit
				Min.	Typ.	Max.	
Zero gate voltage collector current	ICES	VGE=0V, VCE=600V		—	—	1.0	mA
Gate-Emitter leakage current	IGES	VCE=0V, VGE=±20V		—	—	200	nA
Gate-Emitter threshold voltage	VGE(th)	VCE=20V, IC=150mA		6.2	6.7	7.7	V
Collector-Emitter saturation voltage	VCE(sat) (terminal)	VGE=15V, IC=150A	TJ=25°C	—	2.05	2.35	V
			TJ=125°C	—	2.30	—	
	VCE(sat) (chip)		TJ=25°C	—	1.80	—	
			TJ=125°C	—	2.05	—	
Input capacitance	Cies	VCE=10V, VGE=0V, f=1MHz		—	12	—	nF
Turn-on time	ton	VCC=300V IC=150A VGE=±15V		—	0.40	1.20	μs
	tr			—	0.22	0.60	
	tr(i)			—	0.16	—	
Turn-off time	toff	RG= 24 Ω		—	0.48	1.20	
	tr			—	0.07	0.45	
Forward on voltage	VF (terminal)	VGE=0V IF=150A	TJ=25°C	—	1.80	2.20	V
			TJ=125°C	—	1.85	—	
	VF (chip)		TJ=25°C	—	1.60	—	
			TJ=125°C	—	1.65	—	
Reverse recovery time	trr	IF=150A		—	—	0.35	μs
Lead resistance, terminal-chip*3	R lead			—	1.39	—	mΩ

*3:Biggest internal terminal resistance among arm.

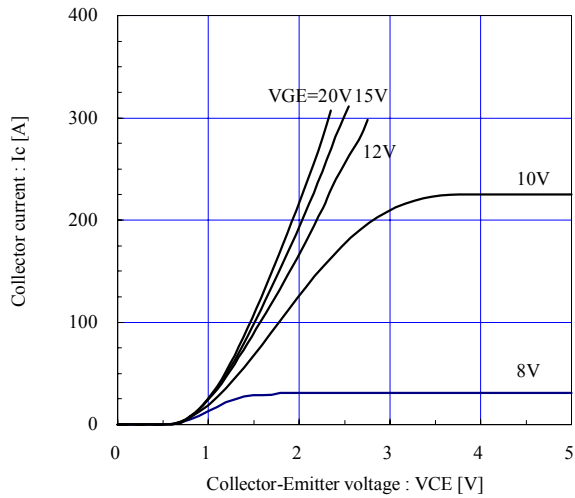
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Unit
			Min.	Typ.	Max.	
Thermal resistance	R _{th(j-c)}	IGBT	—	—	0.25	°C/W
	R _{th(j-c)}	FWD	—	—	0.46	°C/W
Contact Thermal resistance	R _{th(c-f)} *4	With thermal compound	—	0.05	—	°C/W

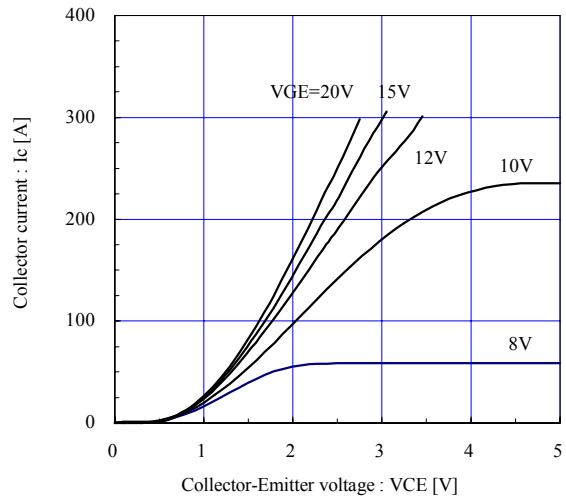
*4 : This is the value which is defined mounting on the additional cooling fin with thermal compound.

Characteristics (Representative)

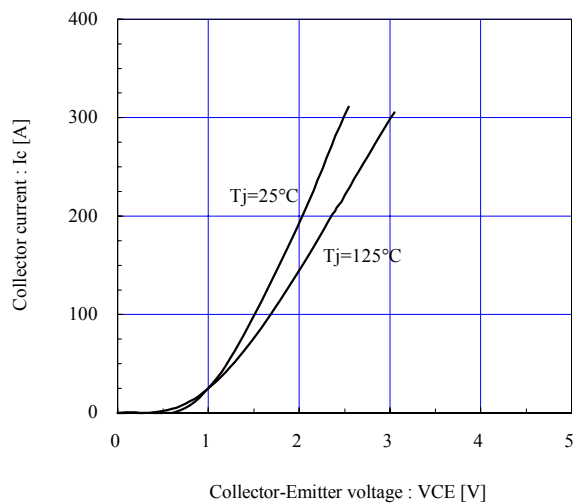
Collector current vs. Collector-Emitter voltage (typ.)
T_j = 25°C / chip



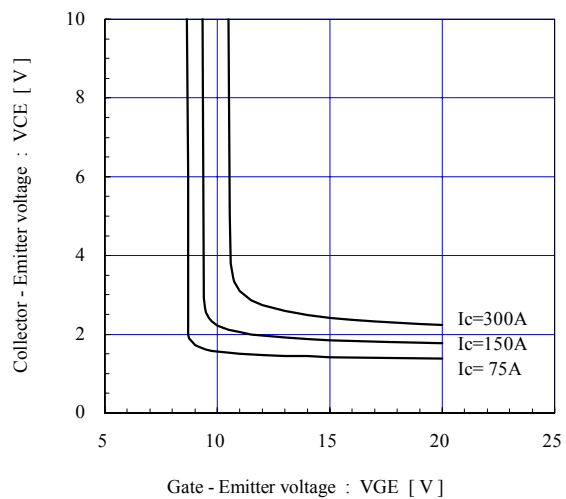
Collector current vs. Collector-Emitter voltage (typ.)
T_j = 125°C / chip



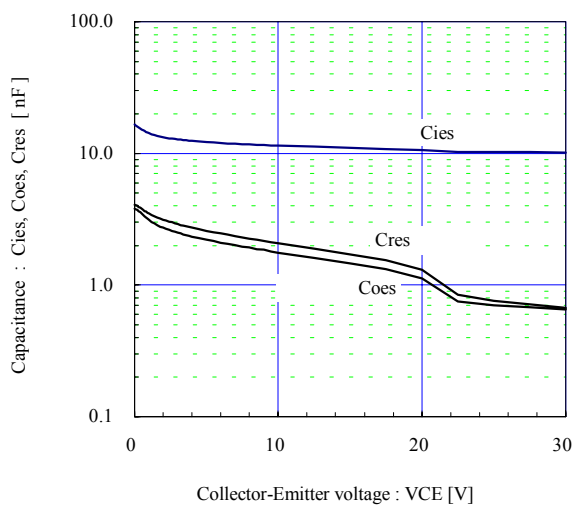
Collector current vs. Collector-Emitter voltage (typ.)
V_{GE} = 15V / chip



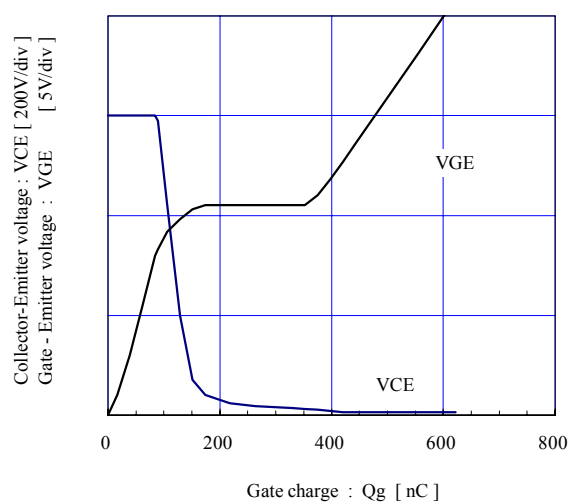
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)
T_j = 25°C / chip



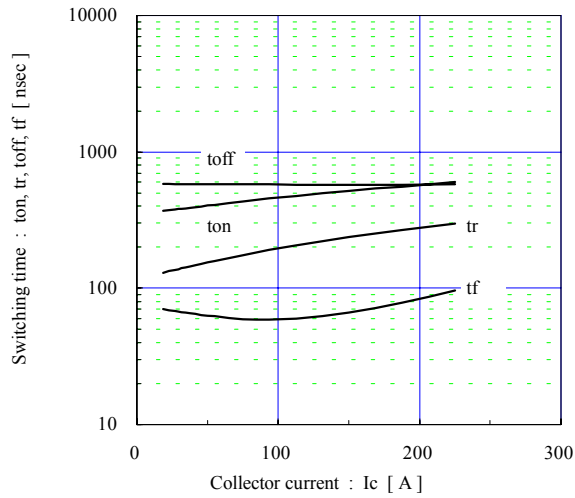
Capacitance vs. Collector-Emitter voltage (typ.)



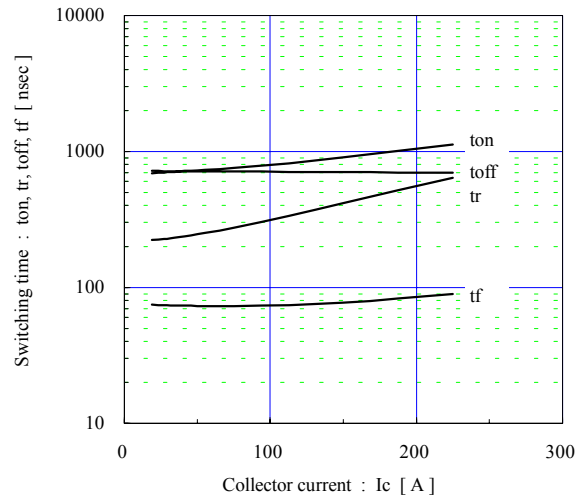
Dynamic Gate charge (typ.)
V_{CC} = 300V, I_c = 150A, T_j = 25°C



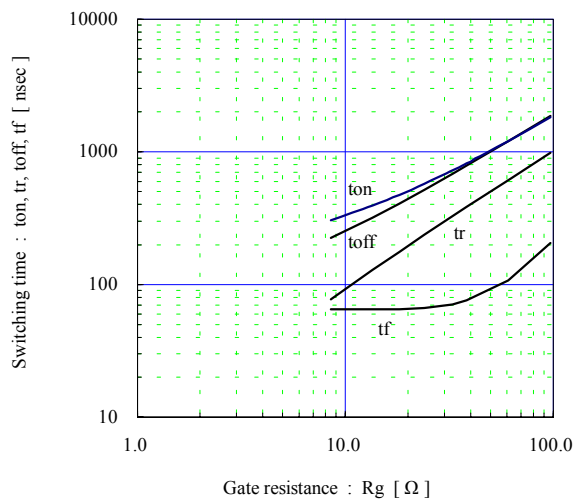
Switching time vs. Collector current (typ.)
 $V_{cc}=300V$, $V_{GE}=\pm 15V$, $R_g=24\Omega$, $T_j=25^\circ C$



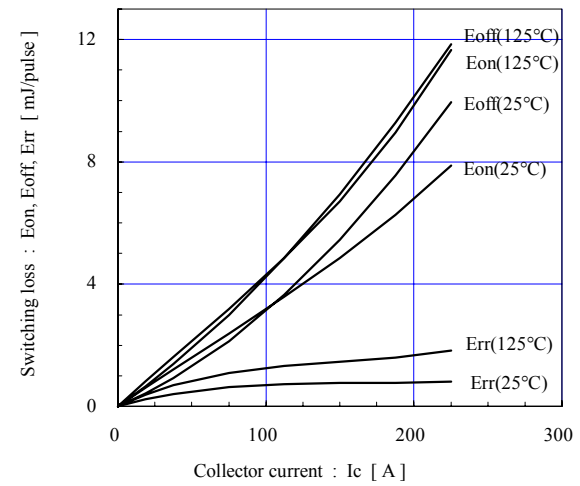
Switching time vs. Collector current (typ.)
 $V_{cc}=300V$, $V_{GE}=\pm 15V$, $R_g=24\Omega$, $T_j=125^\circ C$



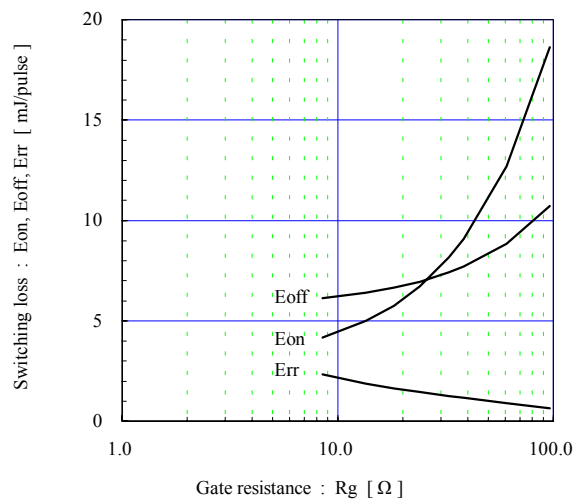
Switching time vs. Gate resistance (typ.)
 $V_{cc}=300V$, $I_c=150A$, $V_{GE}=\pm 15V$, $T_j=25^\circ C$



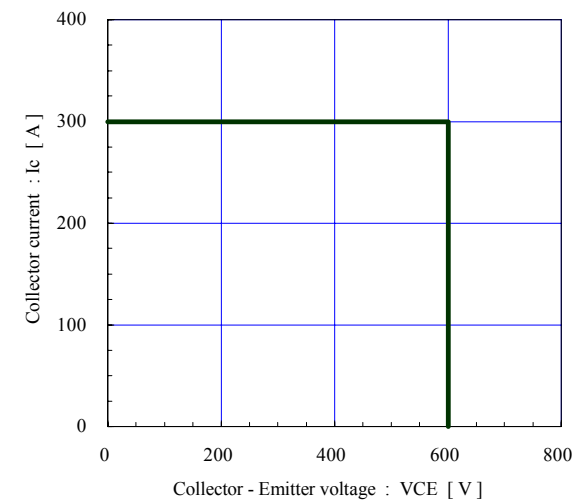
Switching loss vs. Collector current (typ.)
 $V_{cc}=300V$, $V_{GE}=\pm 15V$, $R_g=24\Omega$

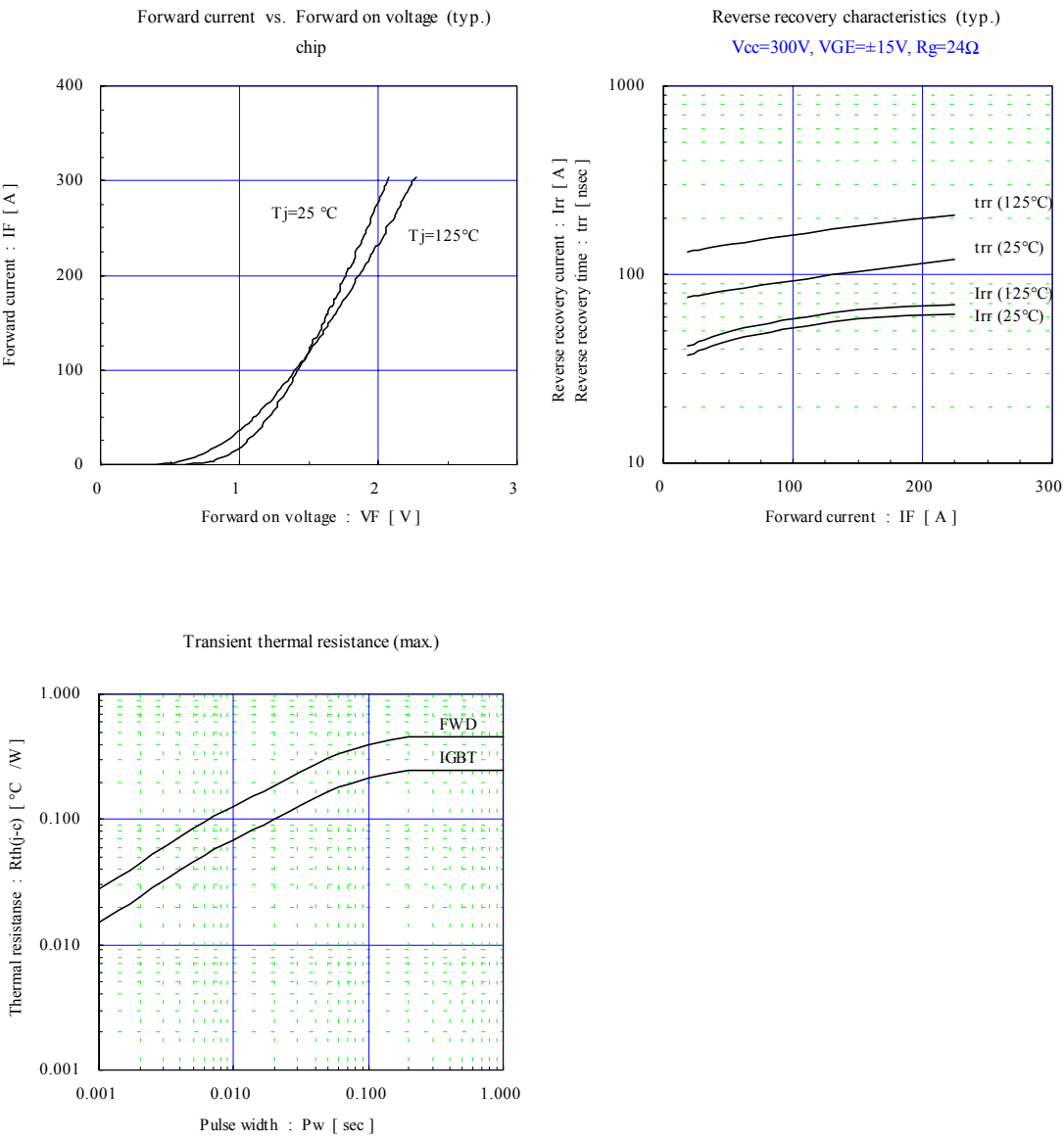


Switching loss vs. Gate resistance (typ.)
 $V_{cc}=300V$, $I_c=150A$, $V_{GE}=\pm 15V$, $T_j=125^\circ C$



Reverse bias safe operating area (max.)
 $+V_{GE}=15V$, $-V_{GE} \leq 15V$, $R_g \geq 24\Omega$, $T_j \leq 125^\circ C$





■ Outline Drawings, mm

M232

